Rachel Angharad Oliver

List of Publications by Year in Descending Order

262 papers	4,590 citations	36 h-index	53 g-index
279 ext. papers	5,134 ext. citations	3.7 avg, IF	5.54 L-index

#	Paper	IF	Citations
262	Influence of Al x Ga1− N nucleation layers on MOVPE-grown zincblende GaN epilayers on 3C-SiC/Si(001). *Journal Physics D: Applied Physics*, **2022**, 55, 175110	3	1
261	Optical emission from focused ion beam milled halide perovskite device cross-sections.. *Microscopy Research and Technique*, **2022**,	2.8	3
260	Investigation of wurtzite formation in MOVPE-grown zincblende GaN epilayers on AlxGa1−N nucleation layers. *Journal of Applied Physics*, **2022**, 131, 115703	2.5	1
259	Decreased Fast Time Scale Spectral Diffusion of a Nonpolar InGaN Quantum Dot. *ACS Photonics*, **2022**, 9, 275-281	6.3	1
258	Photocurrent detection of radially polarized optical vortex with hot electrons in Au/GaN. *Applied Physics Letters*, **2022**, 120, 202101	3.4	
257	Nitride single photon sources. *Frontiers of Nanoscience*, **2021**, 439-471	0.7	
256	Dislocations at coalescence boundaries in heteroepitaxial GaN/sapphire studied after the epitaxial layer has completely coalesced. *Ultramicroscopy*, **2021**, 231, 113258	3.1	2
255	Defect structures in (001) zincblende GaN/3C-SiC nucleation layers. *Journal of Applied Physics*, **2021**, 129, 155306	2.5	6
254	Using pulsed mode scanning electron microscopy for cathodoluminescence studies on hybrid perovskite films. *Nano Express*, **2021**, 2, 024002	2	2
253	Effect of Micron-scale Photoluminescence Variation on Droop Measurements in InGaN/GaN Quantum Wells. *Journal of Physics: Conference Series*, **2021**, 1919, 012011	0.3	
252	Photoluminescence efficiency of zincblende InGaN/GaN quantum wells. *Journal of Applied Physics*, **2021**, 129, 175702	2.5	4
251	Pure single-photon emission from an InGaN/GaN quantum dot. *APL Materials*, **2021**, 9, 061106	5.7	5
250	Thermal stress modelling of diamond on GaN/III-Nitride membranes. *Carbon*, **2021**, 174, 647-661	10.4	7
249	Gender issues in fundamental physics: Strumia bibliometric analysis fails to account for key confounders and confuses correlation with causation. *Quantitative Science Studies*, **2021**, 2, 263-272	3.8	2
248	Origin(s) of Anomalous Substrate Conduction in MOVPE-Grown GaN HEMTs on Highly Resistive Silicon. *ACS Applied Electronic Materials*, **2021**, 3, 813-824	4	3
247	Combined SEM-CL and STEM investigation of green InGaN quantum wells. *Journal Physics D: Applied Physics*, **2021**, 54, 165107	3	
246	Directly correlated microscopy of trench defects in InGaN quantum wells. *Ultramicroscopy*, **2021**, 231, 113255	3.1	1

245	The effect of thermal annealing on the optical properties of Mg-doped zincblende GaN epilayers. *Journal of Applied Physics*, **2021**, 130, 085705	2.5	2
244	Multimicroscopy of cross-section zincblende GaN LED heterostructure. *Journal of Applied Physics*, **2021**, 130, 115705	2.5	0
243	Effect of Si-doped InGaN underlayers on photoluminescence efficiency and recombination dynamics in InGaN/GaN quantum wells. *Journal Physics D: Applied Physics*, **2021**, 54, 475104	3	1
242	The relationship between the three-dimensional structure of porous GaN distributed Bragg reflectors and their birefringence. *Journal of Applied Physics*, **2020**, 127, 193101	2.5	4
241	Dislocations as channels for the fabrication of sub-surface porous GaN by electrochemical etching. *APL Materials*, **2020**, 8, 031115	5.7	7
240	Non-polar nitride single-photon sources. *Journal of Optics (United Kingdom)*, **2020**, 22, 073001	1.7	1
239	GaN-on-diamond technology platform: Bonding-free membrane manufacturing process. *AIP Advances*, **2020**, 10, 035306	1.5	8
238	Cross-shaped markers for the preparation of site-specific transmission electron microscopy lamellae using focused ion beam techniques. *Ultramicroscopy*, **2020**, 212, 112970	3.1	1
237	Polar (In,Ga)N/GaN Quantum Wells: Revisiting the Impact of Carrier Localization on the Green Gap Problem. *Physical Review Applied*, **2020**, 13,	4.3	20
236	Halide Homogenization for High-Performance Blue Perovskite Electroluminescence. *Research*, **2020**, 2020, 9017871	7.8	20
235	Porous nitride semiconductors reviewed. *Journal Physics D: Applied Physics*, **2020**, 53, 383002	3	11
234	Efficient light-emitting diodes from mixed-dimensional perovskites on a fluoride interface. *Nature Electronics*, **2020**, 3, 704-710	28.4	67
233	Alloy segregation at stacking faults in zincblende GaN heterostructures. *Journal of Applied Physics*, **2020**, 128, 145703	2.5	6
232	Stacking fault-associated polarized surface-emitted photoluminescence from zincblende InGaN/GaN quantum wells. *Applied Physics Letters*, **2020**, 117, 032103	3.4	5
231	Crystalline Interlayers for Reducing the Effective Thermal Boundary Resistance in GaN-on-Diamond. *ACS Applied Materials & Interfaces*, **2020**,	9.5	13
230	Ti Alloyed -GaO: Route towards Wide Band Gap Engineering. *Micromachines*, **2020**, 11,	3.3	6
229	Effects of microstructure and growth conditions on quantum emitters in gallium nitride. *APL Materials*, **2019**, 7, 081106	5.7	10
228	Insight into the impact of atomic- and nano-scale indium distributions on the optical properties of InGaN/GaN quantum well structures grown on m-plane freestanding GaN substrates. *Journal of Applied Physics*, **2019**, 125, 225704	2.5	3

227	Light-output enhancement of InGaN light emitting diodes regrown on nanoporous distributed Bragg reflector substrates. *Japanese Journal of Applied Physics*, **2019**, 58, SCCC14	1.4	5
226	Optical properties of c-Plane InGaN/GaN single quantum wells as a function of total electric field strength. *Japanese Journal of Applied Physics*, **2019**, 58, SCCB09	1.4	3
225	Investigation of stacking faults in MOVPE-grown zincblende GaN by XRD and TEM. *Journal of Applied Physics*, **2019**, 125, 105303	2.5	11
224	Optical and structural properties of dislocations in InGaN. *Journal of Applied Physics*, **2019**, 125, 165701	2.5	8
223	Spectral diffusion time scales in InGaN/GaN quantum dots. *Applied Physics Letters*, **2019**, 114, 112109	3.4	16
222	Investigation of MOVPE-grown zincblende GaN nucleation layers on 3C-SiC/Si substrates. *Journal of Crystal Growth*, **2019**, 524, 125167	1.6	2
221	Thick, Adherent Diamond Films on AlN with Low Thermal Barrier Resistance. *ACS Applied Materials & Interfaces*, **2019**, 11, 40826-40834	9.5	31
220	InGaN as a Substrate for AC Photoelectrochemical Imaging. *Sensors*, **2019**, 19,	3.8	7
219	Encapsulation of methylammonium lead bromide perovskite in nanoporous GaN. *APL Materials*, **2019**, 7, 021107	5.7	12
218	Impact of alloy fluctuations and Coulomb effects on the electronic and optical properties of c-plane GaN/AlGaN quantum wells. *Scientific Reports*, **2019**, 9, 18862	4.9	6
217	Structural characterization of porous GaN distributed Bragg reflectors using x-ray diffraction. *Journal of Applied Physics*, **2019**, 126, 213109	2.5	2
216	Nanoscale structural and chemical analysis of F-implanted enhancement-mode InAlN/GaN heterostructure field effect transistors. *Journal of Applied Physics*, **2018**, 123, 024902	2.5	2
215	Nanoscopic insights into the effect of silicon on core-shell InGaN/GaN nanorods: Luminescence, composition, and structure. *Journal of Applied Physics*, **2018**, 123, 045103	2.5	8
214	Resonant photoluminescence studies of carrier localisation in c-plane InGaN/GaN quantum well structures. *Journal of Physics Condensed Matter*, **2018**, 30, 175303	1.8	8
213	Structure and magnetic properties of an epitaxial Fe(110)/MgO(111)/GaN(0001) heterostructure. *Journal of Applied Physics*, **2018**, 123, 103901	2.5	
212	Atom probe tomography of nitride semiconductors. *Scripta Materialia*, **2018**, 148, 75-81	5.6	25
211	Ultra-low-threshold InGaN/GaN quantum dot micro-ring lasers. *Optics Letters*, **2018**, 43, 799-802	3	19
210	Vertical leakage mechanism in GaN on Si high electron mobility transistor buffer layers. *Journal of Applied Physics*, **2018**, 124, 055702	2.5	20

209	Atomic Resolution Imaging of Dislocations in AlGaN and the Efficiency of UV LEDs. *Microscopy and Microanalysis*, **2018**, 24, 4-5	0.5	
208	Alloy fluctuations at dislocations in III-nitrides: identification and impact on optical properties **2018**,		1
207	Characterisation of InGaN by Photoconductive Atomic Force Microscopy. *Materials*, **2018**, 11,	3.5	5
206	What is red? On the chromaticity of orange-red InGaN/GaN based LEDs. *Journal of Applied Physics*, **2018**, 124, 183102	2.5	18
205	Porous AlGaN-Based Ultraviolet Distributed Bragg Reflectors. *Materials*, **2018**, 11,	3.5	7
204	Recombination from polar InGaN/GaN quantum well structures at high excitation carrier densities. *Physical Review B*, **2018**, 98,	3.3	8
203	Effects of a Si-doped InGaN Underlayer on the Optical Properties of InGaN/GaN Quantum Well Structures with Different Numbers of Quantum Wells. *Materials*, **2018**, 11,	3.5	5
202	Photomodulated Reflectivity Measurement of Free-Carrier Dynamics in InGaN/GaN Quantum Wells. *ACS Photonics*, **2018**, 5, 4437-4446	6.3	4
201	Improvement of single photon emission from InGaN QDs embedded in porous micropillars. *Applied Physics Letters*, **2018**, 113, 101107	3.4	15
200	Effect of growth temperature and V/III-ratio on the surface morphology of MOVPE-grown cubic zincblende GaN. *Journal of Applied Physics*, **2018**, 124, 105302	2.5	13
199	On-Chip Thermal Insulation Using Porous GaN. *Proceedings (mdpi)*, **2018**, 2, 776	0.3	2
198	Effect of stacking faults on the photoluminescence spectrum of zincblende GaN. *Journal of Applied Physics*, **2018**, 123, 185705	2.5	9
197	Evolution of the m-Plane Quantum Well Morphology and Composition within a GaN/InGaN Core□Shell Structure. *Crystal Growth and Design*, **2017**, 17, 474-482	3.5	8
196	X-ray reflectivity method for the characterization of InGaN/GaN quantum well interface. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600664	1.3	5
195	Carrier localization in the vicinity of dislocations in InGaN. *Journal of Applied Physics*, **2017**, 121, 013104	2.5	36
194	The atomic structure of polar and non-polar InGaN quantum wells and the green gap problem. *Ultramicroscopy*, **2017**, 176, 93-98	3.1	19
193	Validity of Vegard□ rule for Al1□InxN (0.08 . *Journal Physics D: Applied Physics*, **2017**, 50, 205107	3	8
192	Structural impact on the nanoscale optical properties of InGaN core-shell nanorods. *Applied Physics Letters*, **2017**, 110, 172105	3.4	19

191	Dielectric behaviour of montmorillonite/cyanoethylated cellulose nanocomposites. *Carbohydrate Polymers*, **2017**, 172, 315-321	10.3	13
190	Theoretical and experimental analysis of radiative recombination lifetimes in nonpolar InGaN/GaN quantum dots. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600675	1.3	14
189	Mechanisms preventing trench defect formation in InGaN/GaN quantum well structures using hydrogen during GaN barrier growth. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600666	1.3	10
188	High-temperature performance of non-polar (11$\bar{2}$0) InGaN quantum dots grown by a quasi-two-temperature method. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600724	1.3	5
187	Photoluminescence studies of cubic GaN epilayers. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600733	1.3	13
186	Defects in III-nitride microdisk cavities. *Semiconductor Science and Technology*, **2017**, 32, 033002	1.8	4
185	Surface Zeta Potential and Diamond Seeding on Gallium Nitride Films. *ACS Omega*, **2017**, 2, 7275-7280	3.9	26
184	X-ray diffraction analysis of cubic zincblende III-nitrides. *Journal Physics D: Applied Physics*, **2017**, 50, 433002	3	26
183	Deterministic optical polarisation in nitride quantum dots at thermoelectrically cooled temperatures. *Scientific Reports*, **2017**, 7, 12067	4.9	10
182	Application of Atom Probe Tomography to Nitride Semiconductors. *Microscopy and Microanalysis*, **2017**, 23, 666-667	0.5	
181	Dislocations in AlGaN: Core Structure, Atom Segregation, and Optical Properties. *Nano Letters*, **2017**, 17, 4846-4852	11.5	23
180	Effects of Wavelength and Defect Density on the Efficiency of (In,Ga)N-Based Light-Emitting Diodes. *Physical Review Applied*, **2017**, 7,	4.3	11
179	Direct generation of linearly polarized single photons with a deterministic axis in quantum dots. *Nanophotonics*, **2017**, 6, 1175-1183	6.3	11
178	Wafer-scale Fabrication of Non-Polar Mesoporous GaN Distributed Bragg Reflectors via Electrochemical Porosification. *Scientific Reports*, **2017**, 7, 45344	4.9	33
177	Stable Speckle Patterns for Nano-scale Strain Mapping up to 700°C. *Experimental Mechanics*, **2017**, 57, 1469-1482	2.6	26
176	Temperature-dependent fine structure splitting in InGaN quantum dots. *Applied Physics Letters*, **2017**, 111, 053101	3.4	4
175	Properties of GaN nanowires with $Sc_xGa_{1-x}N$ insertion. *Physica Status Solidi (B): Basic Research*, **2017**, 254, 1600740	1.3	
174	Polarisation-controlled single photon emission at high temperatures from InGaN quantum dots. *Nanoscale*, **2017**, 9, 9421-9427	7.7	22

173	Highly polarized electrically driven single-photon emission from a non-polar InGaN quantum dot. *Applied Physics Letters*, **2017**, 111, 251108	3.4	6
172	The ABC model of recombination reinterpreted: Impact on understanding carrier transport and efficiency droop in InGaN/GaN light emitting diodes. *Journal of Applied Physics*, **2017**, 122, 234505	2.5	20
171	Impact of high energy electrons on nitrides for nanocathodoluminescence **2016**, 1044-1045		
170	Structural and optical properties of (112 2) InGaN quantum wells compared to (0001) and (112 0). *Semiconductor Science and Technology*, **2016**, 31, 085007	1.8	4
169	A study of the optical and polarisation properties of InGaN/GaN multiple quantum wells grown on -plane and -plane GaN substrates. *Science and Technology of Advanced Materials*, **2016**, 17, 736-743	7.1	5
168	Structure and composition of non-polar (11-20) InGaN nanorings grown by modified droplet epitaxy. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 840-844	1.3	1
167	Critical Assessment 23: Gallium nitride-based visible light-emitting diodes. *Materials Science and Technology*, **2016**, 32, 737-745	1.5	8
166	Nanocathodoluminescence reveals the mitigation of the Stark shift in InGaN quantum wells by silicon doping **2016**, 562-563		
165	Molecular beam epitaxy of free-standing bulk wurtzite AlxGa1-xN layers using a highly efficient RF plasma source. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2016**, 13, 217-220		1
164	Nanocomposites of TiO cyanoethylated cellulose with ultra high dielectric constants. *Nanotechnology*, **2016**, 27, 195402	3.4	17
163	Ultrafast, Polarized, Single-Photon Emission from m-Plane InGaN Quantum Dots on GaN Nanowires. *Nano Letters*, **2016**, 16, 7779-7785	11.5	23
162	Theoretical and experimental analysis of the photoluminescence and photoluminescence excitation spectroscopy spectra of m-plane InGaN/GaN quantum wells. *Applied Physics Letters*, **2016** , 109, 223102	3.4	6
161	Comparative studies of efficiency droop in polar and non-polar InGaN quantum wells. *Applied Physics Letters*, **2016**, 108, 252101	3.4	17
160	A comparison of the optical properties of InGaN/GaN multiple quantum well structures grown with and without Si-doped InGaN prelayers. *Journal of Applied Physics*, **2016**, 119, 055708	2.5	12
159	The nature of carrier localisation in polar and nonpolar InGaN/GaN quantum wells. *Journal of Applied Physics*, **2016**, 119, 181505	2.5	56
158	The microstructure of non-polar a-plane (11 2 0) InGaN quantum wells. *Journal of Applied Physics*, **2016**, 119, 175703	2.5	19
157	Radiative recombination mechanisms in polar and non-polar InGaN/GaN quantum well LED structures. *Applied Physics Letters*, **2016**, 109, 151110	3.4	29
156	Local carrier recombination and associated dynamics in m-plane InGaN/GaN quantum wells probed by picosecond cathodoluminescence. *Applied Physics Letters*, **2016**, 109, 232103	3.4	7

155	Nano-cathodoluminescence reveals the effect of electron damage on the optical properties of nitride optoelectronics and the damage threshold. *Journal of Applied Physics*, **2016**, 120, 165704	2.5	8
154	Nitride quantum light sources. *Europhysics Letters*, **2016**, 113, 38001	1.6	11
153	Self-assembled Multilayers of Silica Nanospheres for Defect Reduction in Non- and Semipolar Gallium Nitride Epitaxial Layers. *Crystal Growth and Design*, **2016**, 16, 1010-1016	3.5	4
152	Effect of QW growth temperature on the optical properties of blue and green InGaN/GaN QW structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2016**, 13, 209-213		4
151	Investigating efficiency droop in InGaN/GaN quantum well structures using ultrafast time-resolved terahertz and photoluminescence spectroscopy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2016**, 13, 252-255		
150	Room temperature PL efficiency of InGaN/GaN quantum well structures with prelayers as a function of number of quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2016**, 13, 248-251		7
149	Effect of electron blocking layers on the conduction and valence band profiles of InGaN/GaN LEDs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2016**, 13, 262-265		1
148	A study of the inclusion of prelayers in InGaN/GaN single- and multiple-quantum-well structures. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 866-872	1.3	14
147	Carrier distributions in InGaN/GaN light-emitting diodes. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 890-894	1.3	5
146	Low-Temperature Growth of Carbon Nanotube Forests Consisting of Tubes with Narrow Inner Spacing Using Co/Al/Mo Catalyst on Conductive Supports. *ACS Applied Materials & Interfaces*, **2015**, 7, 16819-27	9.5	23
145	SCM and SIMS investigations of unintentional doping in III-nitrides. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2015**, 12, 403-407		6
144	Nanocathodoluminescence Reveals Mitigation of the Stark Shift in InGaN Quantum Wells by Si Doping. *Nano Letters*, **2015**, 15, 7639-43	11.5	28
143	Indium clustering in a-plane InGaN quantum wells as evidenced by atom probe tomography. *Applied Physics Letters*, **2015**, 106, 072104	3.4	40
142	Effect of the barrier growth mode on the luminescence and conductivity micron scale uniformity of InGaN light emitting diodes. *Journal of Applied Physics*, **2015**, 117, 115705	2.5	7
141	Non-polar InGaN quantum dot emission with crystal-axis oriented linear polarization. *Applied Physics Letters*, **2015**, 106, 171108	3.4	11
140	Ultra-low threshold gallium nitride photonic crystal nanobeam laser. *Applied Physics Letters*, **2015**, 106, 231104	3.4	19
139	Practical Issues for Atom Probe Tomography Analysis of III-Nitride Semiconductor Materials. *Microscopy and Microanalysis*, **2015**, 21, 544-56	0.5	22
138	Growth of non-polar InGaN quantum dots with an underlying AlN/GaN distributed Bragg reflector by metal-organic vapour phase epitaxy. *Superlattices and Microstructures*, **2015**, 88, 480-488	2.8	3

137	Structural, electronic, and optical properties of m-plane InGaN/GaN quantum wells: Insights from experiment and atomistic theory. *Physical Review B*, **2015**, 92,	3.3	48
136	Difference in linear polarization of biaxially strained InxGa1□N alloys on nonpolar a-plane and m-plane GaN. *Physical Review B*, **2015**, 92,	3.3	3
135	Effects of quantum well growth temperature on the recombination efficiency of InGaN/GaN multiple quantum wells that emit in the green and blue spectral regions. *Applied Physics Letters*, **2015**, 107, 132106	3.4	48
134	Optical studies of non-polar m-plane () InGaN/GaN multi-quantum wells grown on freestanding bulk GaN. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 965-970	1.3	13
133	Microstructural dependency of optical properties of m-plane InGaN multiple quantum wells grown on 2□misoriented bulk GaN substrates. *Applied Physics Letters*, **2015**, 107, 082104	3.4	3
132	Effect of Threading Dislocations on the Quality Factor of InGaN/GaN Microdisk Cavities. *ACS Photonics*, **2015**, 2, 137-143	6.3	23
131	Investigation of unintentional indium incorporation into GaN barriers of InGaN/GaN quantum well structures. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 928-935	1.3	14
130	Cathodoluminescence hyperspectral imaging of trench-like defects in InGaN/GaN quantum well structures. *Journal Physics D: Applied Physics*, **2014**, 47, 135107	3	9
129	Effects of an InGaN prelayer on the properties of InGaN/GaN quantum well structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 710-713		10
128	An investigation into defect reduction techniques for growth of non-polar GaN on sapphire. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 541-544		15
127	High excitation density recombination dynamics in InGaN/GaN quantum well structures in the droop regime. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 694-697		1
126	Non-polar (11$ bar 2 $0) InGaN quantum dots with short exciton lifetimes grown by metal-organic vapour phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 698-701		4
125	High temperature stability in non-polar (11$ bar 2 $0) InGaN quantum dots: Exciton and biexciton dynamics. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 702-705		17
124	The effects of varying threading dislocation density on the optical properties of InGaN/GaN quantum wells. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 750-753		8
123	Bias dependence and correlation of the cathodoluminescence and electron beam induced current from an InGaN/GaN light emitting diode. *Journal of Applied Physics*, **2014**, 116, 033105	2.5	15
122	Distinctive signature of indium gallium nitride quantum dot lasing in microdisk cavities. *Proceedings of the National Academy of Sciences of the United States of America*, **2014**, 111, 14042-6	11.5	32
121	Coincident electron channeling and cathodoluminescence studies of threading dislocations in GaN. *Microscopy and Microanalysis*, **2014**, 20, 55-60	0.5	23
120	Growth of non-polar (11-20) InGaN quantum dots by metal organic vapour phase epitaxy using a two temperature method. *APL Materials*, **2014**, 2, 126101	5.7	16

119	Observations of Rabi oscillations in a non-polar InGaN quantum dot. *Applied Physics Letters*, **2014**, 104, 263108	3.4	16
118	Polarized photoluminescence excitation spectroscopy of a-plane InGaN/GaN multiple quantum wells grown on r-plane sapphire. *Journal of Applied Physics*, **2014**, 115, 113106	2.5	11
117	The effects of Si-doped prelayers on the optical properties of InGaN/GaN single quantum well structures. *Applied Physics Letters*, **2014**, 105, 092106	3.4	16
116	The impact of trench defects in InGaN/GaN light emitting diodes and implications for the "green gap" problem. *Applied Physics Letters*, **2014**, 105, 112110	3.4	39
115	Low temperature carrier redistribution dynamics in InGaN/GaN quantum wells. *Journal of Applied Physics*, **2014**, 115, 113505	2.5	16
114	Evaluation of growth methods for the heteroepitaxy of non-polar (11$\bar{2}$0) GAN on sapphire by MOVPE. *Journal of Crystal Growth*, **2014**, 408, 32-41	1.6	12
113	The impact of growth parameters on trench defects in InGaN/GaN quantum wells. *Physica Status Solidi (A) Applications and Materials Science*, **2014**, 211, 740-743	1.6	6
112	Dynamics of carrier redistribution processes in InGaN/GaN quantum well structures. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 738-741		2
111	Electron Channeling Contrast Imaging of Defects in III-Nitride Semiconductors. *Microscopy and Microanalysis*, **2014**, 20, 1024-1025	0.5	
110	Alloy content determination of fully strained and partially relaxed semi-polar group III-nitrides by x-ray diffraction. *Journal of Applied Physics*, **2013**, 114, 053520	2.5	8
109	Low temperature growth of ultra-high mass density carbon nanotube forests on conductive supports. *Applied Physics Letters*, **2013**, 103, 073116	3.4	44
108	The impact of gross well width fluctuations on the efficiency of GaN-based light emitting diodes. *Applied Physics Letters*, **2013**, 103, 141114	3.4	45
107	Correlations between the morphology and emission properties of trench defects in InGaN/GaN quantum wells. *Journal of Applied Physics*, **2013**, 113, 073505	2.5	28
106	Towards a better understanding of trench defects in InGaN/GaN quantum wells. *Journal of Physics: Conference Series*, **2013**, 471, 012042	0.3	2
105	High excitation carrier density recombination dynamics of InGaN/GaN quantum well structures: Possible relevance to efficiency droop. *Applied Physics Letters*, **2013**, 102, 022106	3.4	27
104	Properties of trench defects in InGaN/GaN quantum well structures. *Physica Status Solidi (A) Applications and Materials Science*, **2013**, 210, 195-198	1.6	12
103	Growth of InGaN quantum dots with AlGaN barrier layers via modified droplet epitaxy. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2013**, 178, 1390-1394	3.1	5
102	The impact of substrate miscut on the morphology of InGaN epitaxial layers subjected to a growth interruption. *Journal of Applied Physics*, **2013**, 113, 063503	2.5	7

101	Low threshold, room-temperature microdisk lasers in the blue spectral range. *Applied Physics Letters*, **2013**, 103, 021112	3.4	48
100	Defect Reduction in Semi-Polar (112 2) Gallium Nitride Grown Using Epitaxial Lateral Overgrowth. *Japanese Journal of Applied Physics*, **2013**, 52, 08JB01	1.4	9
99	Non-polar (11-20) InGaN quantum dots with short exciton lifetimes grown by metal-organic vapor phase epitaxy. *Applied Physics Letters*, **2013**, 102, 251905	3.4	32
98	Fundamentals of X-ray Diffraction Characterisation of Strain in GaN Based Compounds. *Japanese Journal of Applied Physics*, **2013**, 52, 08JB29	1.4	8
97	Origins of Spectral Diffusion in the Micro-Photoluminescence of Single InGaN Quantum Dots. *Japanese Journal of Applied Physics*, **2013**, 52, 08JE01	1.4	13
96	Carrier Density Dependent Localization and Consequences for Efficiency Droop in InGaN/GaN Quantum Well Structures. *Japanese Journal of Applied Physics*, **2013**, 52, 08JK10	1.4	13
95	Evidence for Dark States in the Temperature Dependent Recombination Dynamics of InGaN/GaN Quantum Wells. *Japanese Journal of Applied Physics*, **2013**, 52, 08JL12	1.4	
94	Growth and optical characterisation of multilayers of InGaN quantum dots. *Journal of Crystal Growth*, **2012**, 338, 262-266	1.6	12
93	The consequences of high injected carrier densities on carrier localization and efficiency droop in InGaN/GaN quantum well structures. *Journal of Applied Physics*, **2012**, 111, 083512	2.5	90
92	The negligible effects of miscut on indium aluminium nitride growth. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 461-464		1
91	Unintentional doping in GaN. *Physical Chemistry Chemical Physics*, **2012**, 14, 9558-73	3.6	44
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